

Silicon PNP Power Transistors

2SA1265N

DESCRIPTION

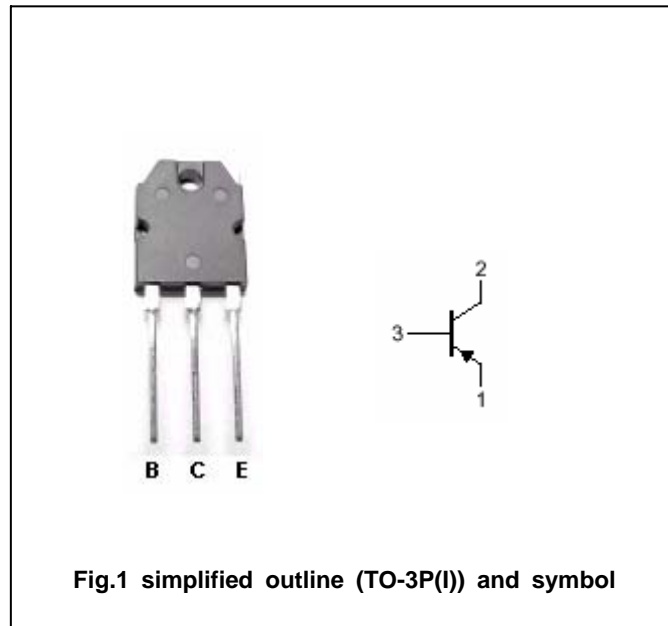
- With TO-3P(I) package
- Complement to type 2SC3182
- 2SA1265 with short pin

APPLICATIONS

- Power amplifier applications

PINNING

| PIN | DESCRIPTION |
|-----|--------------------------------------|
| 1 | Emitter |
| 2 | Collector;connected to mounting base |
| 3 | Base |

Absolute maximum ratings($T_a=25^\circ\text{C}$)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|-----------|---------------------------|------------------------|---------|------------------|
| V_{CBO} | Collector-base voltage | Open emitter | -140 | V |
| V_{CEO} | Collector-emitter voltage | Open base | -140 | V |
| V_{EBO} | Emitter-base voltage | Open collector | -5 | V |
| I_C | Collector current | | -10 | A |
| I_B | Base current | | -1 | A |
| P_T | Total power dissipation | $T_C=25^\circ\text{C}$ | 100 | W |
| T_j | Junction temperature | | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage temperature | | -55~150 | $^\circ\text{C}$ |

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CHARACTERISTICS

T_j=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|---|------|------|------|------|
| V _{(BR)CEO} | Collector-emitter breakdown voltage | I _C =-50mA, I _B =0 | -140 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =-7A; I _B =-0.7A | | -0.8 | -2.0 | V |
| V _{BE} | Base-emitter voltage | I _C =-5A; V _{CE} =-5V | | -1.0 | -1.5 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =-140V; I _E =0 | | | -5 | μ A |
| I _{EBO} | Emitter cut-off current | V _{EB} =-5V; I _C =0 | | | -5 | μ A |
| h _{FE-1} | DC current gain | I _C =-1A; V _{CE} =-5V | 55 | | 160 | |
| h _{FE-2} | DC current gain | I _C =-5A; V _{CE} =5V | 35 | | | |
| f _T | Transition frequency | I _C =-1A; V _{CE} =-5V | | 30 | | MHz |
| C _{ob} | Output capacitance | I _E =0; V _{CB} =10V; f=1MHz | | 480 | | pF |

◆ h_{FE-1} Classifications

| | |
|--------|--------|
| R | O |
| 55-110 | 80-160 |

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PACKAGE OUTLINE

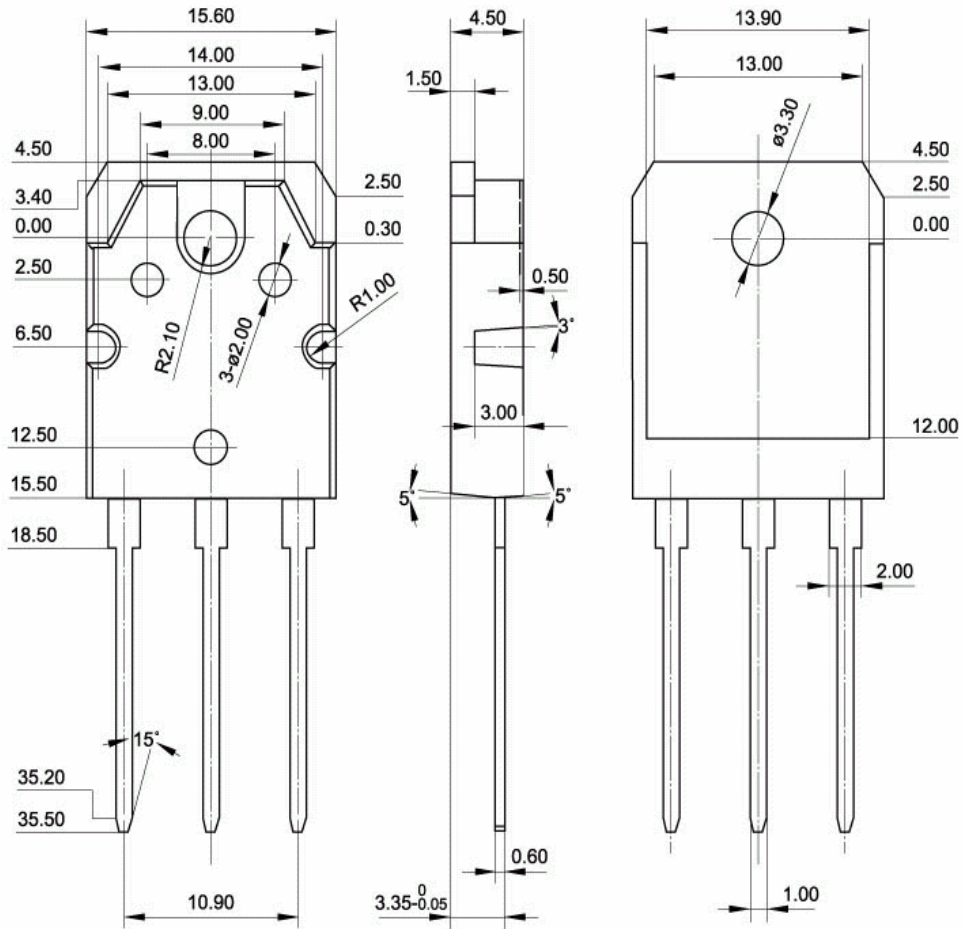


Fig.2 Outline dimensions(unindicated tolerance: ±0.10 mm)

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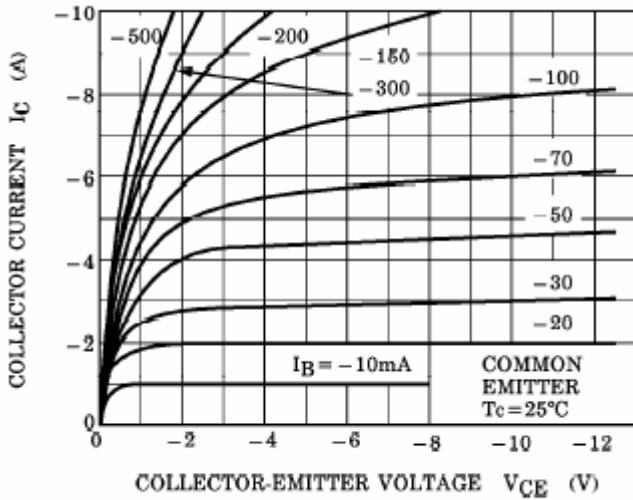


Fig.3 DC current Gain

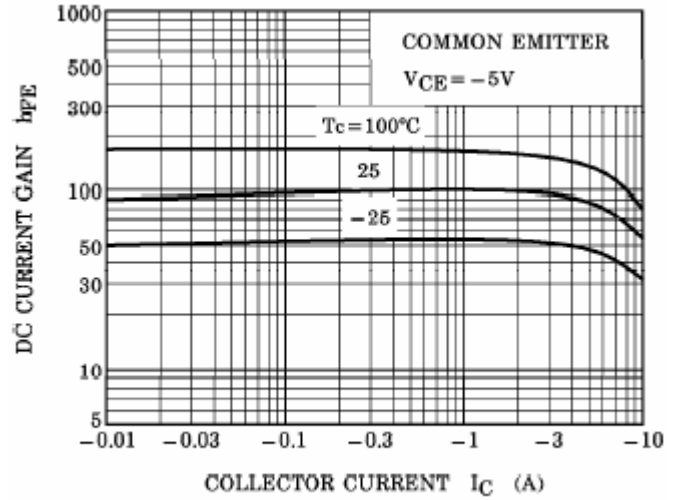


Fig.4 DC current Gain

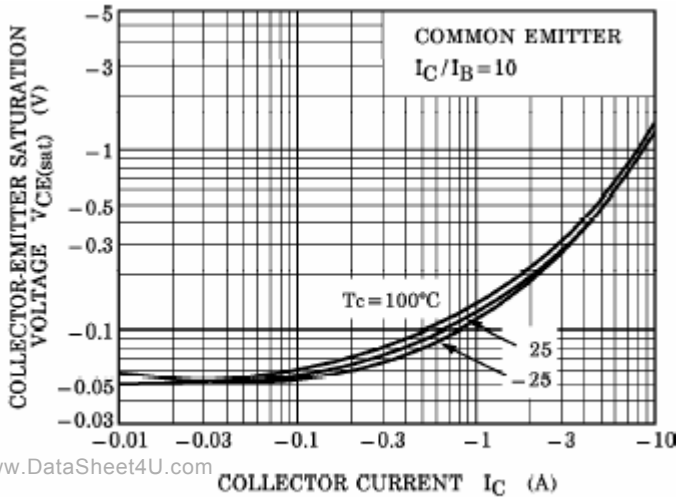


Fig.5 Collector-Emitter Saturation Voltage

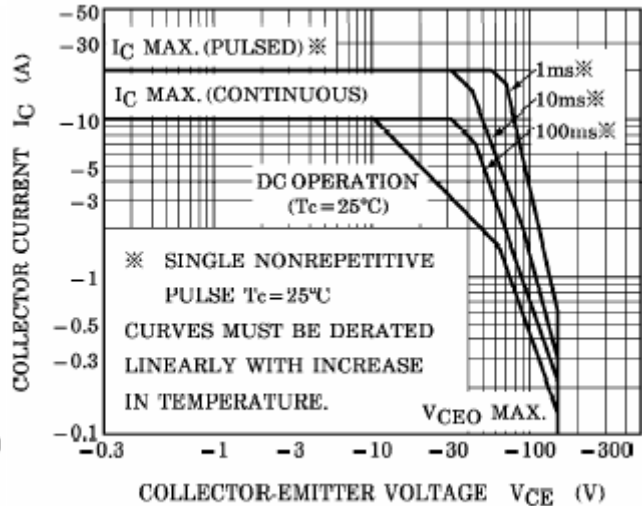


Fig.6 Safe Operating Area